

REMARKS

The Examiner stated: "The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed. The following title is suggested: METHOD FOR FABRICATING A TRIPLE DAMASCENE FUSE." In response, Applicants have amended the title as the Examiner has suggested.

The Examiner objected to claims 11 to 15 as allegedly being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The Examiner indicated that claims 16 to 20 would be allowable if rewritten or amended to overcome the rejection(s) under 35 U.S.C. §112, second paragraph, set forth in this Office action. Applicants gratefully acknowledge the Examiner's indication of allowable subject matter.

The Examiner rejected claims 10 to 20 under 35 U.S.C. §112, second paragraph, as allegedly being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

The Examiner rejected claim 10 under 35 U.S.C. §102(b) as allegedly being anticipated by Yeh (U.S. Patent No. 5,169,802).

Applicants respectfully traverse the §112 and §102 rejections with the following arguments.

35 U.S.C. §112

The Examiner suggested that line 9 of claim 10 should be amended to change "removing said first dielectric layer from over said mandrel" to -- removing said second dielectric layer from over said mandrel.-- Applicants have so amended claim 10.

The Examiner suggested that line 9 of claim 16 should be amended to change "removing said first dielectric layer from over said mandrel" to -- removing said second dielectric layer from over said mandrel.-- Applicants have so amended claim 16.

35 U.S.C. §102

The Examiner rejected claim 10 stating "Yeh discloses in FIG. 3 to 9 a method for fabricating a semiconductor device, comprising: providing a substrate (10, 11 and 12); forming a first dielectric layer 14 on a top surface of said substrate; forming a dielectric mandrel 27 on a top surface of said first dielectric layer 14; forming a second dielectric layer 15 on top of said mandrel 27 and a top surface of said first dielectric layer 14; forming contact openings 24 and 25 down to said substrate in said first and second dielectric layers 14 and 15 on opposite sides of said mandrel 27; removing said second dielectric layer 15 from over said mandrel 27 between said contact openings 24 and 25 to form a trough 22; and filling said trough 22 and contact openings 24 and 25 with a conductor 16."

Applicants respectfully contend that Yeh does not anticipate claim 10, as amended, because Yeh does not teach each and every feature of claim 10. For example, Yeh does not teach "leaving dielectric material of said second dielectric layer between said mandrel and each of said contact openings;"

In Yeh FIG. 8, contact opening 24 abuts mandrel 27 on the left, contact opening 25 abuts mandrel 27 on the right and trench 22 abuts the top of mandrel 27. In Yeh, FIG. 8, no material of the second dielectric layer 15 exists between mandrel 27 and each of contact openings 24 and 25.

Based on the preceding arguments, Applicants respectfully maintain that Yeh does not anticipate claim 10, and that claim 10 is in condition for allowance. Since claims 30-34 depend from claim 10, Applicants contend claims 30-34 are also in condition for allowance.

CONCLUSION

Based on the preceding arguments, Applicants respectfully believe that all pending claims and the entire application meet the acceptance criteria for allowance and therefore request favorable action. If the Examiner believes that anything further would be helpful to place the application in better condition for allowance, Applicants invites the Examiner to contact Applicants' representative at the direct dial telephone number listed below. The Director is hereby authorized to charge and/or credit Deposit Account 09-0456.

Respectfully submitted,
FOR: Daubenspeck et al.

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